



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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SOT23 SILICON PLANAR VARIABLE CAPACITANCE DIODE

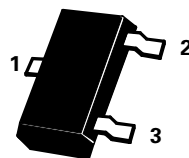
FMMV105G

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PIN CONFIGURATION



PARTMARKING DETAILS
FMMV105G – 4EZ



SOT23

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Power Dissipation at $T_{amb}=25^{\circ}\text{C}$	P_{tot}	330	mW
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Reverse Breakdown Voltage	V_{BR}	30			V	$I_R = 10\mu\text{A}$
Reverse current	I_R			10	nA	$V_R = 28\text{V}$
Series Inductance	L_S		3.0		nH	$f=250\text{MHz}$
Diode Capacitance Temperature Coefficient	T_{CC}		280		ppm/ $^{\circ}\text{C}$	$V_R = 3\text{V}, f=1\text{MHz}$

TUNING CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Diode Capacitance	C_d	1.8		2.8	pF	$V_R = 25\text{V}, f=1\text{MHz}$
Capacitance Ratio	C_d / C_d	4.0		6.0		$V_R = 3\text{V}/25\text{V}, f=1\text{MHz}$
Figure of MERIT	Q	250	350			$V_R = 3\text{V}, f=50\text{MHz}$

Spice parameter data is available upon request for this device